

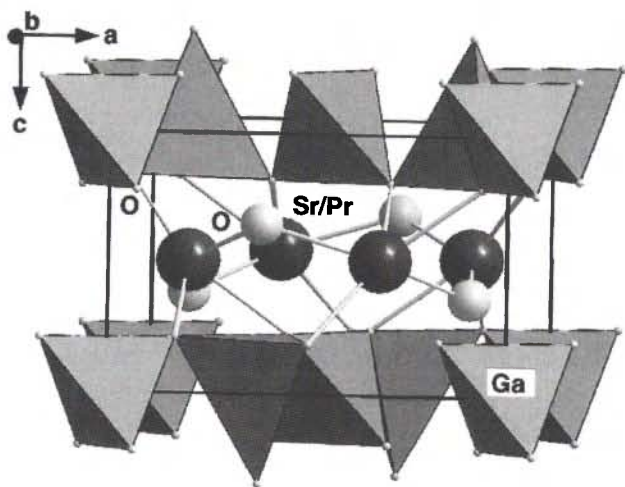
# Crystal structure of strontium praseodym trigallium heptaoxide, $(\text{Sr}_{0.5}\text{Pr}_{0.5})_2\text{Ga}_3\text{O}_7$

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## Abstract

$\text{Ga}_3\text{O}_7\text{PrSr}$ , tetragonal,  $P\bar{4}2_1m$  (No. 113),  $a = 8.0198(2) \text{ \AA}$ ,  $c = 5.2991(1) \text{ \AA}$ ,  $V = 340.8 \text{ \AA}^3$ ,  $Z = 2$ ,  $R(P) = 0.026$ ,  $wR(P) = 0.040$ ,  $R(I) = 0.025$ ,  $T = 295 \text{ K}$ .

## Source of material

$\text{SrPrGa}_3\text{O}_7$  was synthesized by melting a mixture of the oxides and carbonates (4N and 5N quality) under flowing nitrogen in an Ir crucible. A mixture containing  $\text{SrO}$ ,  $\text{Pr}_2\text{O}_3$  and  $\text{Ga}_2\text{O}_3$  in a molar ratio of 2:1:3 was used. The solidified melt was homogeneous and of green color. Because of the incongruent melting of  $\text{SrPrGaO}_4$  - one of the most favoured candidates for substrates for high- $T_c$  superconductors - a shift in the melt composition during the growth process takes place. In consequence,  $\text{SrPrGa}_3\text{O}_7$  is formed in the multiphase residual melt [1].

Starting atomic coordinates for the refinement were taken from  $\text{SrLaCa}_3\text{O}_7$  [2]. The displacement parameters of all atoms were fixed to reliable values.

**Table 1.** Data collection and handling.

Powder:	green
Wavelength:	Cu $K\alpha$ radiation (1.54059 Å)
$\mu$ :	771.1 $\text{cm}^{-1}$
Diffractometer:	Stoe Stadi P
Scan mode:	transmission Debye-Scherrer mode
$2\theta_{\text{max}}$ , stepwidth:	89.98°, 0.02
$N(\text{points})_{\text{measured}}$	3750
$N(hkl)_{\text{measured}}$	104
$N(\text{param})_{\text{refined}}$	39
Program:	RIETAN-97 [3]

**Table 2.** Atomic coordinates and displacement parameters (in  $\text{Å}^2$ ).

Atom	Site	Occ.	x	y	z	$U_{\text{iso}}$
Sr(1)	4e	0.5	0.1621(9)	$x+1/2$	0.509(3)	0.006
Pr(1)	4e	0.5	0.1621	$x+1/2$	0.509	0.006
Ga(1)	4e		0.644(1)	$x+1/2$	0.975(5)	0.009
Ga(2)	2a		0	0	0	0.009
O(1)	8f		0.084(5)	0.160(6)	0.212(7)	0.012
O(2)	4e		0.634(7)	$x+1/2$	0.356(8)	0.012
O(3)	2c		0	1/2	0.193(7)	0.012

## References

1. Uecker, R.; Reiche, P.; Ganschow, S.; Wilde, P.-M.; Uecker, D.-C.; Worzala, H.; Schultze, D.: Growth conditions and composition of  $\text{SrPrGaO}_4$  single crystals. *J. Cryst. Growth* **174** (1997) 320.
2. Steins, M.; Schmitz, W.; Uecker, R.; Doerschel, J.: Crystal Structure of strontium lanthanum trigallium heptaoxide,  $(\text{Sr}_{0.5}\text{La}_{0.5})_2\text{Ga}_3\text{O}_7$ . *Z. Kristallogr. NCS* **212** (1997) 76.
3. Izumi, F.: "The Rietveld Method", ed. by R. A. Young, Oxford University Press, Oxford 1993.

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